

BSS138PW

60 V, 320 mA N-channel Trench MOSFET Rev. 1 — 2 November 2010

Product data sheet

Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT323 (SC-70) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- AEC-Q101 qualified

1.3 Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_{amb} = 25 ^{\circ}C$	-	-	60	V
V_{GS}	gate-source voltage	$T_{amb} = 25 ^{\circ}C$	-	-	±20	V
I_D	drain current	T_{amb} = 25 °C; V_{GS} = 10 V	[1] -	-	320	mA
R _{DSon}	drain-source on-state resistance	$T_j = 25 ^{\circ}\text{C};$ $V_{GS} = 10 \text{V};$ $I_D = 300 \text{mA}$	<u>[2]</u> -	0.9	1.6	Ω

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



^[2] Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.01.$

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2. Pinning information

Table 2. Pinning

	3			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		5
2	S	source	3	D
3	D	drain	1 2	G

3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BSS138PW	SC-70	plastic surface-mounted package; 3 leads	SOT323		

4. Marking

Table 4. Marking codes

Type number	Marking code[1]
BSS138PW	XJ*

^{[1] * =} placeholder for manufacturing site code

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

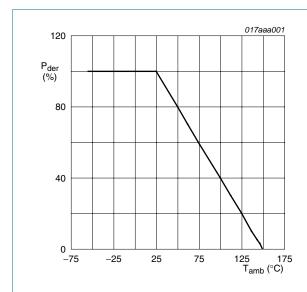
Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_{amb} = 25 ^{\circ}C$	-	60	V
V_{GS}	gate-source voltage	T _{amb} = 25 °C	-	±20	V
I_D	drain current	$V_{GS} = 10 \text{ V}$	<u>[1]</u>		
		T _{amb} = 25 °C	-	320	mA
		T _{amb} = 100 °C	-	200	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$	-	1.2	Α

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Table 5. Limiting values ...continued
In accordance with the Absolute Maximum Rating System (IEC 60134).

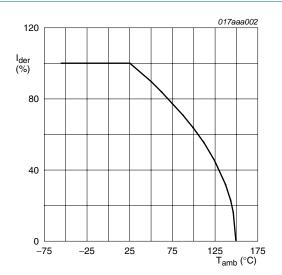
Symbol	Parameter	Conditions	Min	Max	Unit
P _{tot} total power dissipation	total power dissipation	T_{amb} = 25 $^{\circ}C$	[2] _	260	mW
		[1] -	310	mW	
		T _{sp} = 25 °C	-	830	mW
Tj	junction temperature			150	°C
T _{amb}	ambient temperature		– 55	+150	°C
T _{stg}	storage temperature		-65	+150	°C
Source-d	rain diode				
I _S	source current	$T_{amb} = 25 ^{\circ}C$	<u>[1]</u> -	280	mA
	· · · · · · · · · · · · · · · · · · ·				

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



 $P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$

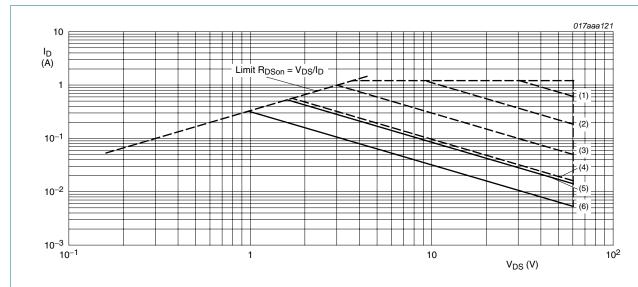
Fig 1. Normalized total power dissipation as a function of ambient temperature



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

Fig 2. Normalized continuous drain current as a function of ambient temperature

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I_{DM} = single pulse

- (1) $t_p = 100 \, \mu s$
- (2) $t_p = 1 \text{ ms}$
- (3) $t_p = 10 \text{ ms}$
- (4) $t_D = 100 \text{ ms}$
- (5) DC; $T_{sp} = 25 \, ^{\circ}C$
- (6) DC; $T_{amb} = 25 \, ^{\circ}C$; drain mounting pad 1 cm²

Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> _	415	480	K/W
			[2] _	350	400	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	150	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

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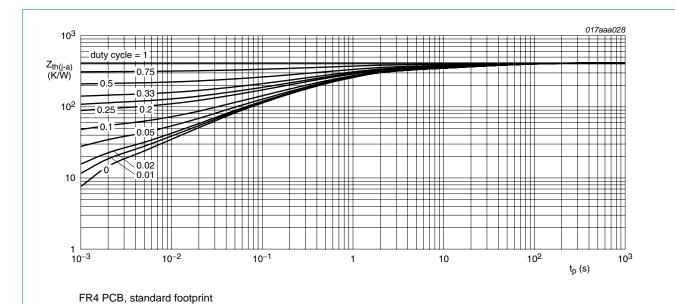
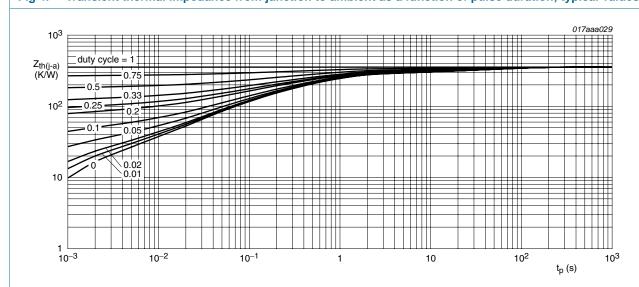


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm²

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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7. Characteristics

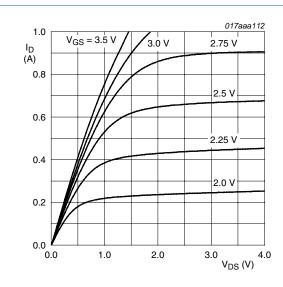
Table 7. Characteristics

 $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 10 \ \mu A; \ V_{GS} = 0 \ V$	60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 250 \ \mu A; \ V_{DS} = V_{GS}$	0.9	1.2	1.5	V
I _{DSS}	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}$				
		T _j = 25 °C	-	-	1	μΑ
		T _j = 150 °C	-	-	10	μΑ
I _{GSS}	gate leakage current	$V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	100	nΑ
R _{DSon}	drain-source on-state		<u>[1]</u>			
	resistance	$V_{GS} = 5 \text{ V}; I_D = 50 \text{ mA}$	-	1	2	Ω
		$V_{GS} = 10 \text{ V}; I_D = 300 \text{ mA}$	-	0.9	1.6	Ω
g _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 200 \text{ mA}$	<u>[1]</u> _	700	-	mS
Dynamic o	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 300 \text{ mA};$ $V_{DS} = 30 \text{ V};$	-	0.72	8.0	nC
Q_{GS}	gate-source charge		-	0.14	-	nC
Q_{GD}	gate-drain charge	$-V_{GS} = 4.5 \text{ V}$	-	0.24	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 10 \text{ V};$	-	38	50	pF
Coss	output capacitance	f = 1 MHz	-	7	-	pF
C _{rss}	reverse transfer capacitance		-	4	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V};$	-	2	6	ns
t _r	rise time	$R_L = 250 \Omega;$	-	3	-	ns
t _{d(off)}	turn-off delay time	$-V_{GS} = 10 \text{ V};$ $R_G = 6 \Omega$	-	9	20	ns
t _f	fall time		-	4	-	ns
Source-dr	ain diode					
V_{SD}	source-drain voltage	$I_S = 115 \text{ mA}; V_{GS} = 0 \text{ V}$	0.47	0.75	1.1	V

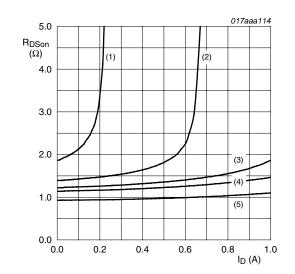
^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.01.$

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 $T_{amb} = 25 \, ^{\circ}C$

Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



T_{amb} = 25 °C

(1) $V_{GS} = 2.0 \text{ V}$

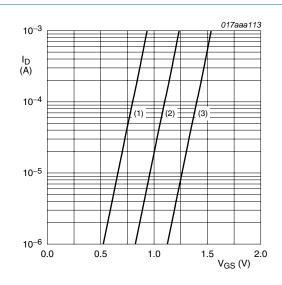
(2) $V_{GS} = 2.5 \text{ V}$

(3) $V_{GS} = 3.0 \text{ V}$

(4) $V_{GS} = 3.5 \text{ V}$

(5) $V_{GS} = 10 \text{ V}$

Fig 8. Drain-source on-state resistance as a function of drain current; typical values



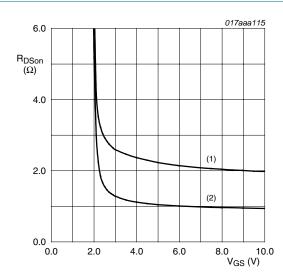
 T_{amb} = 25 °C; V_{DS} = 5 V

(1) minimum values

(2) typical values

(3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage



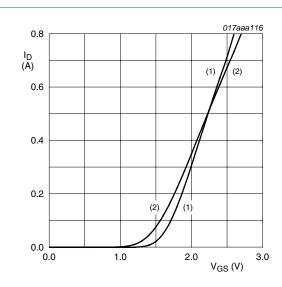
 $I_D = 300 \text{ mA}$

(1) $T_{amb} = 150 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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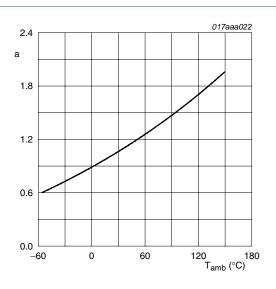


$$V_{DS} > I_D \times R_{DSon}$$

(1)
$$T_{amb} = 25 \,^{\circ}C$$

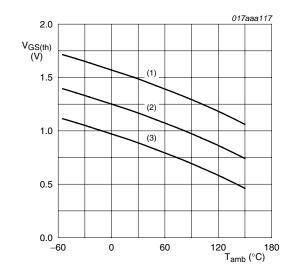
(2)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

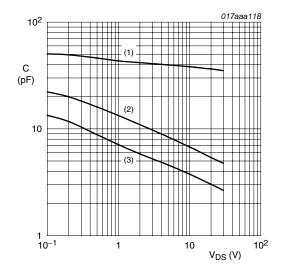
Fig 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig 12. Gate-source threshold voltage as a function of ambient temperature

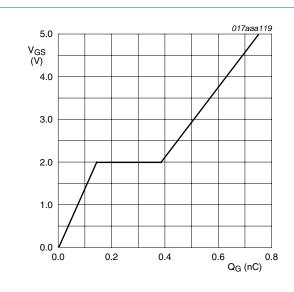


f = 1 MHz; V_{GS} = 0 V

- (1) C_{iss}
- (2) Coss
- (3) C_{rss}

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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 I_D = 300 mA; V_{DS} = 30 V; T_{amb} = 25 °C

Fig 14. Gate-source voltage as a function of gate charge; typical values

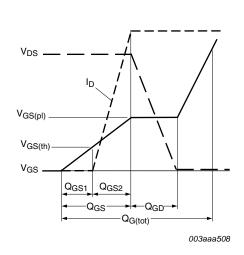
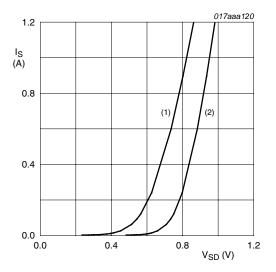


Fig 15. Gate charge waveform definitions



$$V_{GS} = 0 V$$

Fig 16. Source current as a function of source-drain voltage; typical values

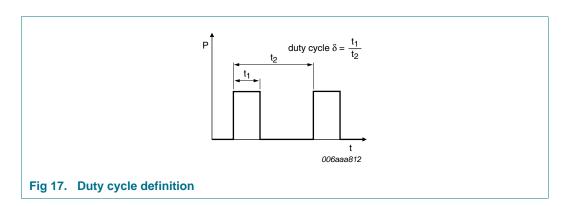
⁽¹⁾ $T_{amb} = 150 \, ^{\circ}C$

⁽²⁾ $T_{amb} = 25 \, ^{\circ}C$

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Test information



8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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9. Package outline

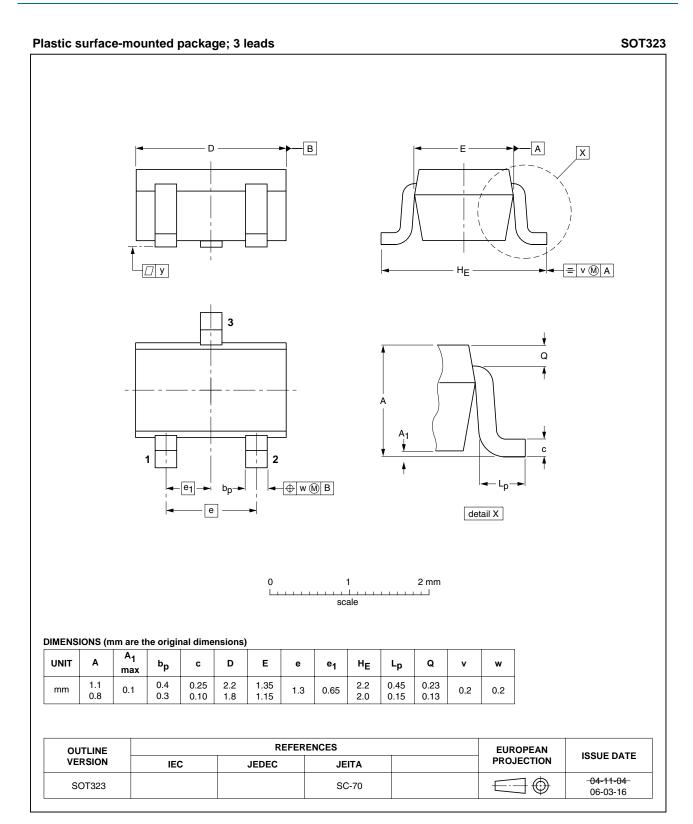


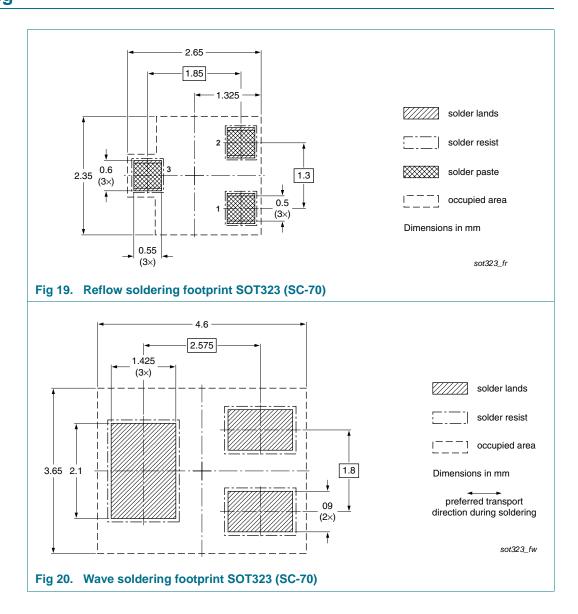
Fig 18. Package outline SOT323 (SC-70)

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10. Soldering



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11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BSS138PW v.1	20101102	Product data sheet	-	-

60 V, 320 mA N-channel Trench MOSFET

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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